

**DUAL WORK FUNCTION SEMICONDUCTOR STRUCTURE
WITH BORDERLESS CONTACT AND METHOD OF
FABRICATING THE SAME**

ABSTRACT OF THE DISCLOSURE

A dual work function semiconductor structure with borderless contact and method of fabricating the same are presented. The structure may include a field effect transistor (FET) having a substantially cap-free gate and a conductive contact to a diffusion adjacent to the cap-free gate, wherein the conductive contact is borderless to the gate. Because the structure is a dual work function structure, the conductive contact is allowed to extend over the cap-free gate without being electrically connected thereto.